DEVICE AND METHOD FOR ACCURATE ETCHING AND REMOVAL OF THIN FILM

ABSTRACT

New device and method are described for accurate etching and removal of thin layer by controlling the surface residence time, thickness and composition of reactant containing film. Etching of silicon dioxide at low pressure using a quartz crystal microbalance is illustrated. Usefullness of the invention in the manufacture of microelectronic devices is shown

Figure. 3A

This Sheet Has Been Replaced

